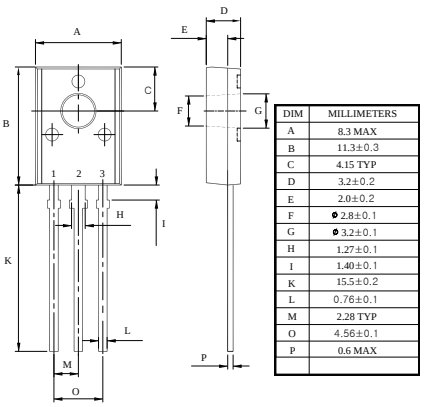
FTB1151 TRANSISTOR (PNP)



DIM	MILLIMETERS
A	8.3 MAX
B	11.3±0.3
C	4.15 TYP
D	3.2±0.2
E	2.0±0.2
F	⌀ 2.8±0.1
G	⌀ 3.2±0.1
H	1.27±0.1
I	1.40±0.1
K	15.5±0.2
L	0.76±0.1
M	2.28 TYP
O	4.56±0.1
P	0.6 MAX

TO-126

FEATURES

- Low Collector-Emitter Saturation Voltage
- Large Collector Current
- High Power Dissipation
- Complement to FTD1691

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current	-5	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	100	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

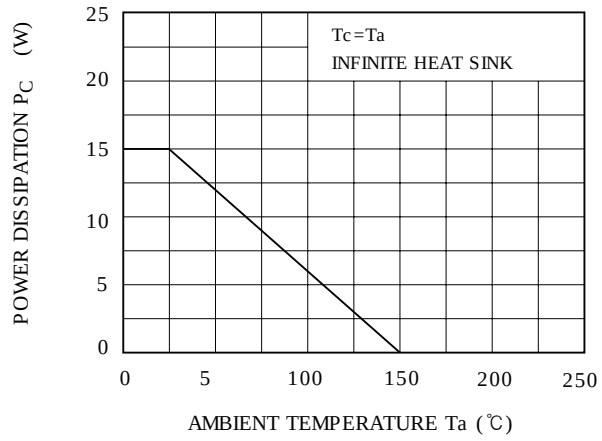
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-7V,I_C=0			-10	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-2A	100		400	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-0.1A	60			
	$h_{FE(3)}$	V_{CE}=-2V, I_C=-5A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A,I_B=-0.2A			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-2A,I_B=-0.2A			-1.2	V

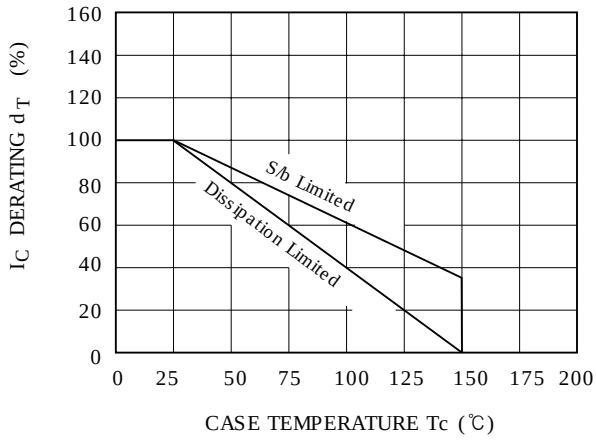
CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y	G
RANGE	100-200	160-320	200-400

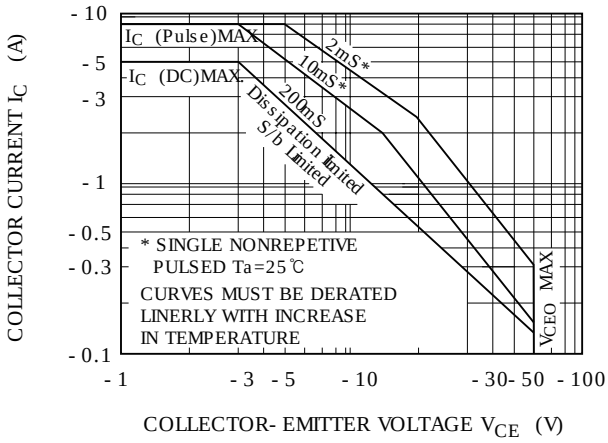
Pc - Ta



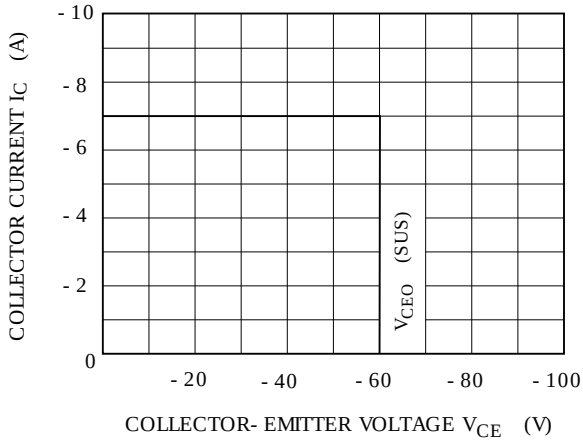
dT - TC



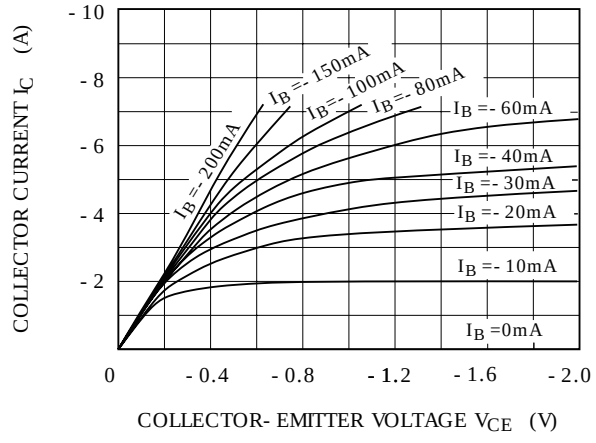
SAFE OPERATING AREA



REVERSE BIAS
SAFE OPERATING AREA



IC - VCE



hFE - IC